优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ Max	I_D Max T_C = +25°C
-20V	6.7mΩ @ V_{GS} = -4.5V	-40A
	9.0mΩ @ V_{GS} = -2.5V	-40A

Description

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Load Switch
- Power Management Functions

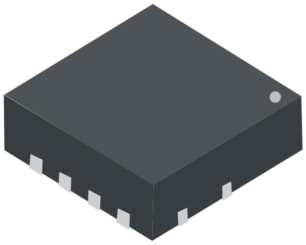
Features

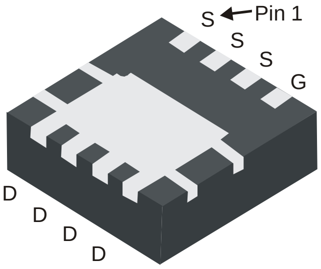
- Low $R_{DS(ON)}$ – ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product

Mechanical Data

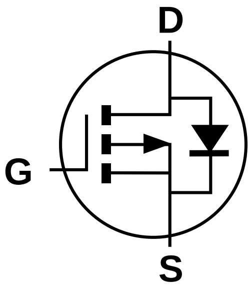
- Case: POWERDI3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 ⓔ3
- Weight: 0.008 grams (Approximate)

POWERDI3333-8


Top View



Bottom View



Equivalent Circuit

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-20	V
Gate-Source Voltage			V_{GSS}	±10	V
Continuous Drain Current (Note 5) V_{GS} = -4.5V	Steady State	T_A = +25°C	I_D	-18.0	A
		T_A = +70°C		-14.5	
		T_C = +25°C		-40	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	-80	A
Maximum Continuous Body Diode Forward Current (Note 5)			I_S	-2.2	A
Avalanche Current (Note 7) L=0.1mH			I_{AS}	-23	A
Avalanche Energy (Note 7) L=0.1mH			E_{AS}	28	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	2.3	W
	T_C = +25°C		41	
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	56	°C/W
	(Note 6)		124	
Thermal Resistance, Junction to Case		$R_{\theta JC}$	6.8	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	-20	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1	µA	V_{DS} = -16V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	-0.4	—	-1.0	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	4.2	6.7	mΩ	V_{GS} = -4.5V, I_D = -15A
		—	5.4	9.0		V_{GS} = -2.5V, I_D = -10A
		—	7	—		V_{GS} = -1.8V, I_D = -1A
Diode Forward Voltage	V_{SD}	—	-0.7	-1.2	V	V_{GS} = 0V, I_S = -10A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	5940	—	pF	V_{DS} = -10V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	835	—		
Reverse Transfer Capacitance	C_{rss}	—	728	—		
Gate Resistance	R_G	—	3.0	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge (VV_{GS} = -4.5V)	Q_g	—	75	—	nC	V_{DD} = -10V, I_D = -20A
Total Gate Charge (V_{GS} = -10V)	Q_g	—	156	—		
Gate-Source Charge	Q_{gs}	—	8.8	—		
Gate-Drain Charge	Q_{gd}	—	22	—		
Turn-On Delay Time	$t_{D(ON)}$	—	10.7	—	ns	V_{GS} = -4.5V, V_{DD} = -10V, R_G = 1Ω, I_D = -10A
Turn-On Rise Time	t_R	—	23	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	121	—		
Turn-Off Fall Time	t_F	—	109	—		
Reverse Recovery Time	t_{RR}	—	60	—	ns	I_F = -10A, di/dt = 100A/µs
Reverse Recovery Charge	Q_{RR}	—	47	—	nC	I_F = -10A, di/dt = 100A/µs

Notes:
5. $R_{\theta JA}$ is determined with the device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
7 .UIS in production with L =0.1mH, T_J = +25°C
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

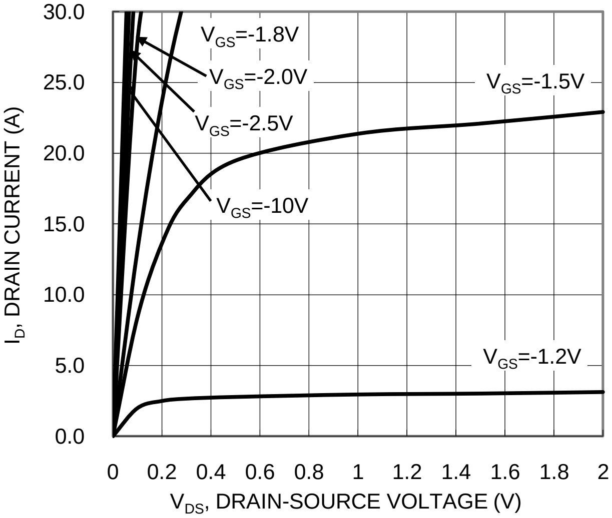


Figure 1. Typical Output Characteristic

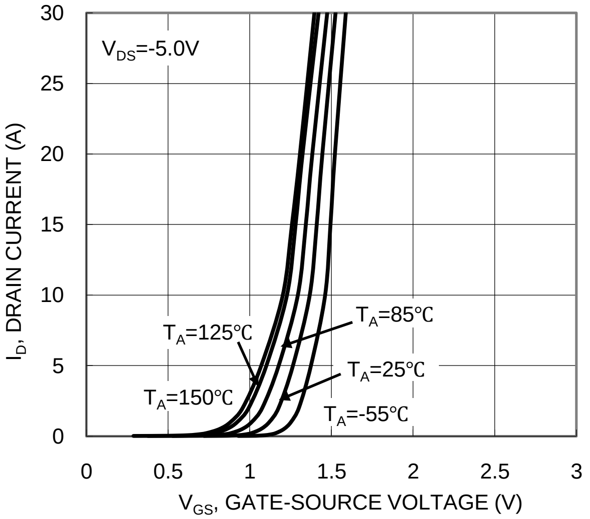


Figure 2. Typical Transfer Characteristic

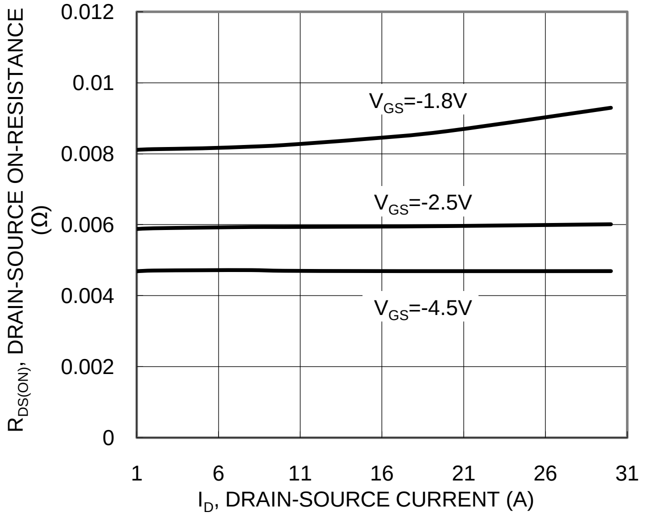


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

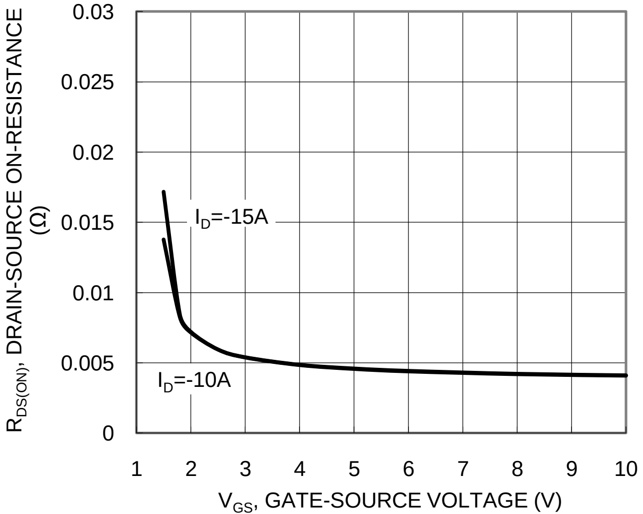


Figure 4. Typical Transfer Characteristic

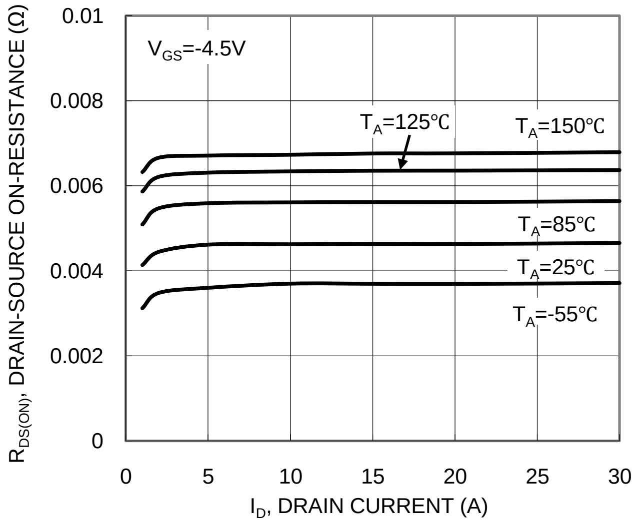


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

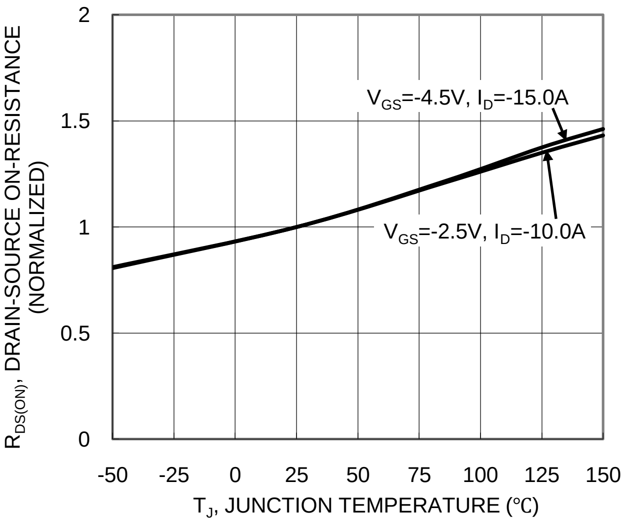


Figure 6. On-Resistance Variation with Temperature

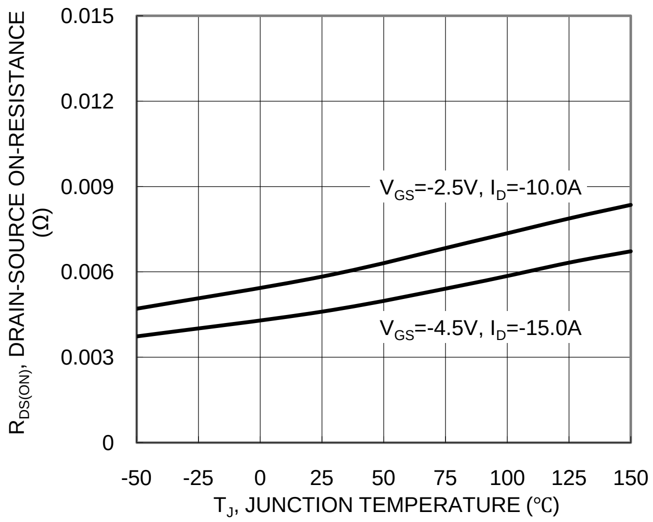


Figure 7. On-Resistance Variation with Temperature

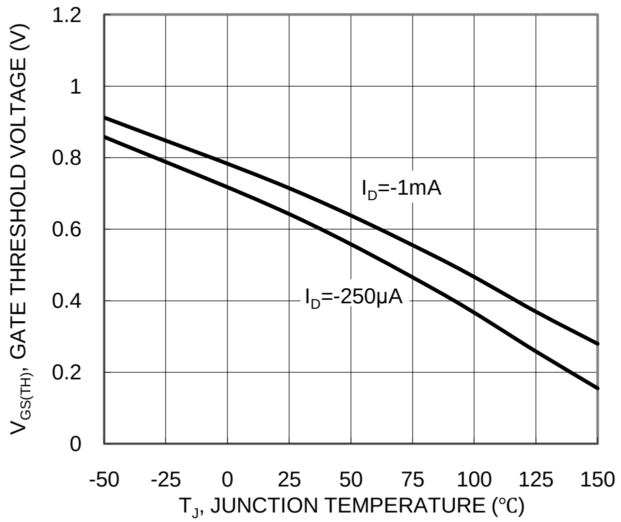


Figure 8. Gate Threshold Variation vs. Junction Temperature

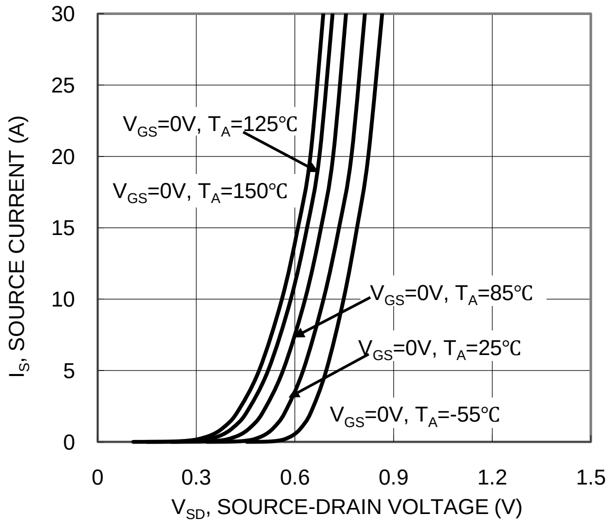


Figure 9. Diode Forward Voltage vs. Current

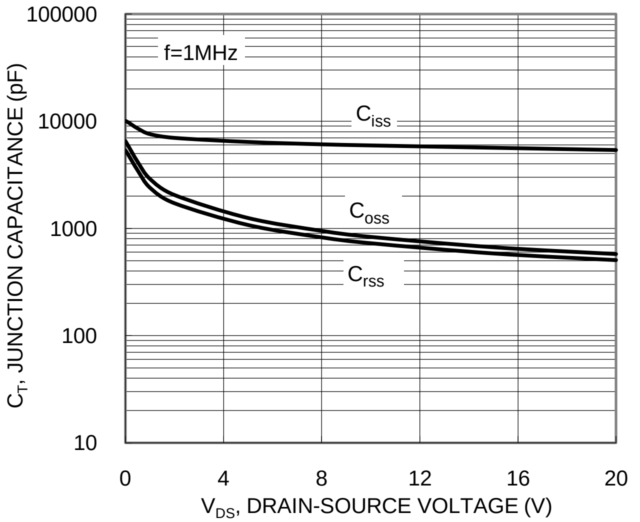


Figure 10. Typical Junction Capacitance

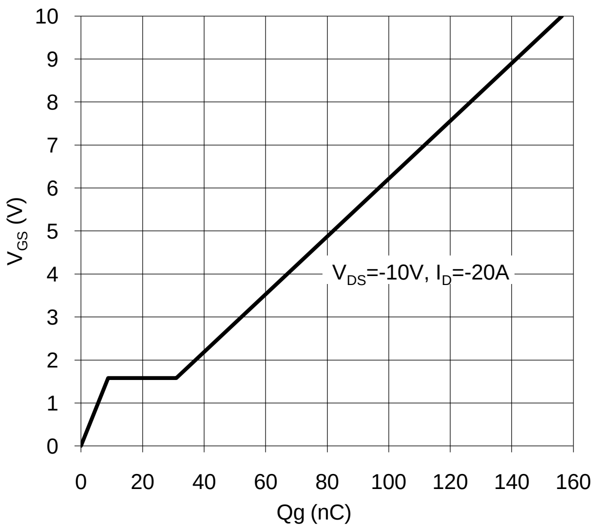


Figure 11. Gate Charge

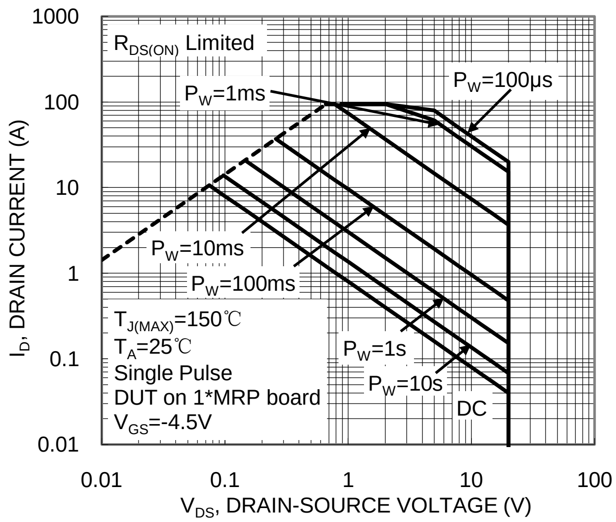


Figure 12. SOA, Safe Operation Area

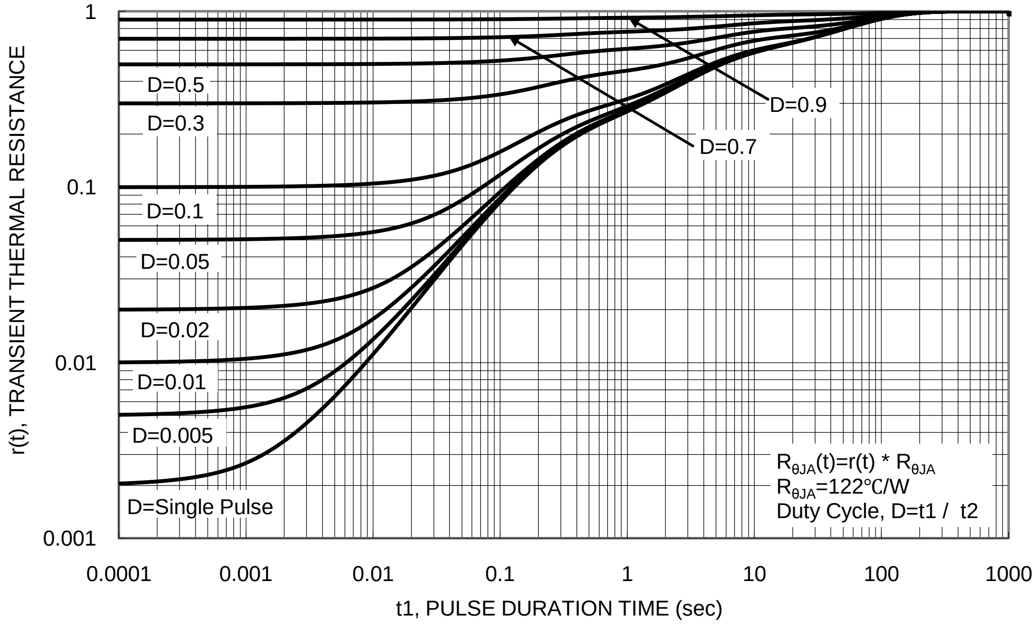
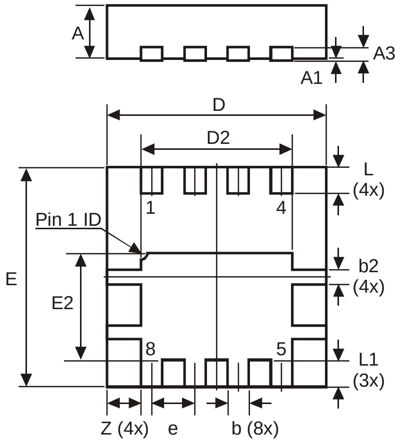


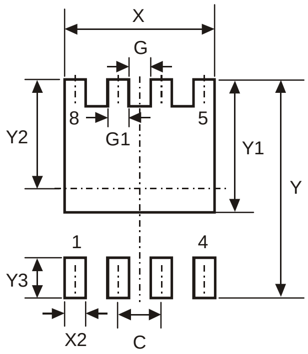
Figure 13. Transient Thermal Resistance

Package Outline Dimensions



POWERDI3333-8			
Dim	**Min**	**Max**	**Typ**
D	3.25	3.35	3.30
E	3.25	3.35	3.30
D2	2.22	2.32	2.27
E2	1.56	1.66	1.61
A	0.75	0.85	0.80
A1	0	0.05	0.02
A3	–	–	0.203
b	0.27	0.37	0.32
b2	–	–	0.20
L	0.35	0.45	0.40
L1	–	–	0.39
e	–	–	0.65
Z	–	–	0.515
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
C	0.650
G	0.230
G1	0.420
Y	3.700
Y1	2.250
Y2	1.850
Y3	0.700
X	2.370
X2	0.420